



**THE DATASHEET OF
PBSS4240T,215**



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Kind regards,

Team Nexperia

DATA SHEET



PBSS4240T

40 V; 2 A NPN low V_{CEsat}
(BISS) transistor

Product data sheet
Supersedes data of 2001 Jul 13

2004 Jan 09

40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Replacement for SOT89/SOT223 standard packaged transistors.

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT23 plastic package. PNP complement: PBSS5240T.

MARKING

| TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|-----------------------------|
| PBSS4240T | ZE* |

Note

- * = p: Made in Hong Kong.
 * = t: Made in Malaysia.
 * = W: Made in China.

ORDERING INFORMATION

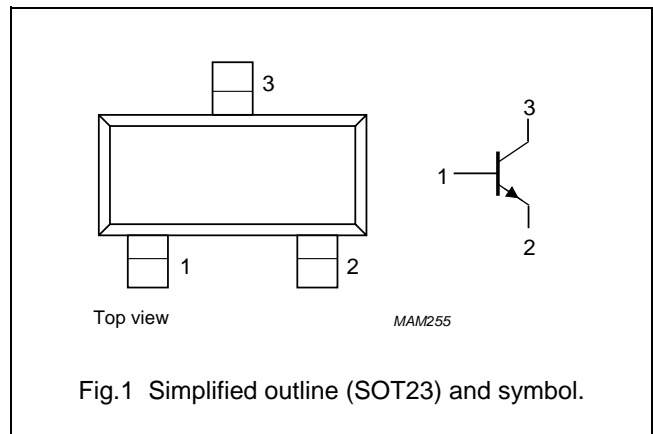
| TYPE NUMBER | PACKAGE | | |
|-------------|---------|--|---------|
| | NAME | DESCRIPTION | VERSION |
| PBSS4240T | - | plastic surface mounted package; 3 leads | SOT23 |

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|-------------|---------------------------|------|------------|
| V_{CEO} | collector-emitter voltage | 40 | V |
| I_{CM} | peak collector current | 3 | A |
| R_{CEsat} | equivalent on-resistance | <200 | m Ω |

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |



40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|-------------------------------|--------------------------------------|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | – | 40 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 40 | V |
| V_{EBO} | emitter-base voltage | open collector | – | 5 | V |
| I_C | collector current (DC) | | – | 2 | A |
| I_{CM} | peak collector current | | – | 3 | A |
| I_{BM} | peak base current | | – | 300 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ °C}$; note 1 | – | 300 | mW |
| | | $T_{amb} \leq 25\text{ °C}$; note 2 | – | 480 | mW |
| T_{stg} | storage temperature | | –65 | +150 | °C |
| T_j | junction temperature | | – | 150 | °C |
| T_{amb} | operating ambient temperature | | –65 | +150 | °C |

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------|---|---------------------|-------|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air; note 1 | 417 | K/W |
| | | in free air; note 2 | 260 | K/W |

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------|--------------------------------------|---|------|------|------|------------------|
| I_{CBO} | collector-base cut-off current | $I_E = 0; V_{CB} = 30\text{ V}$ | – | – | 100 | nA |
| | | $I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$ | – | – | 50 | μA |
| I_{EBO} | emitter-base cut-off current | $I_C = 0; V_{EB} = 4\text{ V}$ | – | – | 100 | nA |
| h_{FE} | DC current gain | $I_C = 100\text{ mA}; V_{CE} = 2\text{ V}$ | 350 | 470 | – | |
| | | $I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$ | 300 | 450 | – | |
| | | $I_C = 1\text{ A}; V_{CE} = 2\text{ V}$ | 300 | 420 | – | |
| | | $I_C = 2\text{ A}; V_{CE} = 2\text{ V}$ | 150 | 250 | – | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 100\text{ mA}; I_B = 1\text{ mA}$ | – | 45 | 70 | mV |
| | | $I_C = 500\text{ mA}; I_B = 50\text{ mA}$ | – | 70 | 100 | mV |
| | | $I_C = 750\text{ mA}; I_B = 15\text{ mA}$ | – | 120 | 180 | mV |
| | | $I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{note 1}$ | – | 130 | 180 | mV |
| | | $I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$ | – | 240 | 320 | mV |
| R_{CEsat} | equivalent on-resistance | $I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$ | – | 140 | <200 | $\text{m}\Omega$ |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$ | – | – | 1.1 | V |
| V_{BEon} | base-emitter turn on voltage | $I_C = 100\text{ mA}; V_{CE} = 2\text{ V}$ | – | – | 0.75 | V |
| C_c | collector capacitance | $I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$ | – | 15 | 20 | pF |
| f_T | transition frequency | $I_C = 100\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$ | 100 | 230 | – | MHz |

Note1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

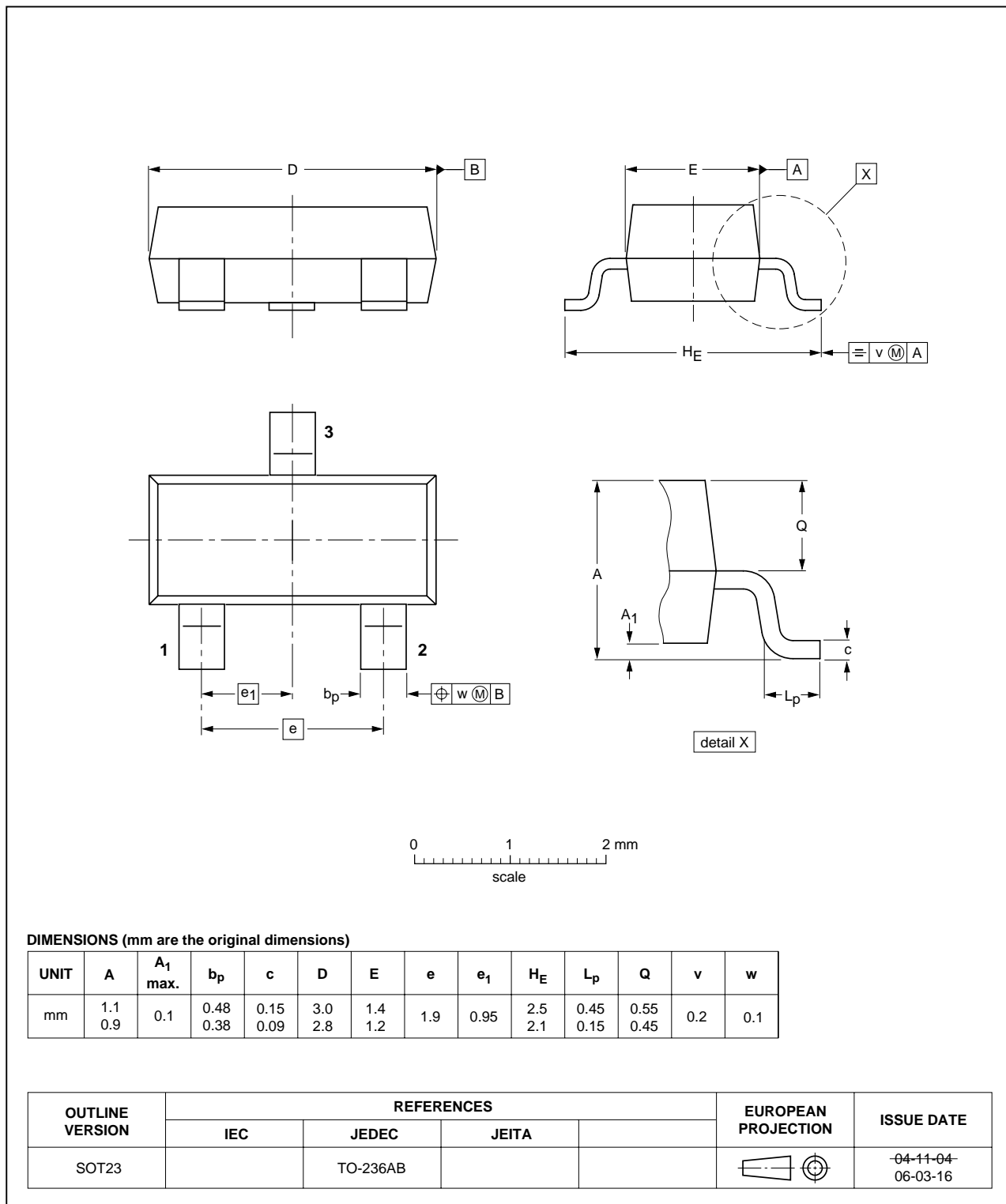
40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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